

SEMICONDUCTOR DEVICE AND ITS DRIVING METHOD

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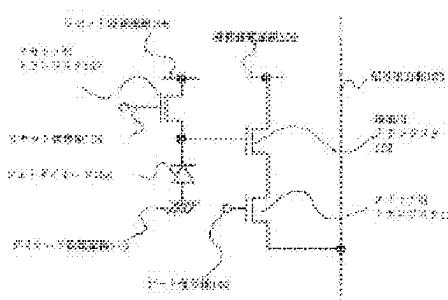
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Application number: JP20000120920 20000421

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Abstract of JP 2001308306 (A)

PROBLEM TO BE SOLVED: To provide a semiconductor device that can reduce the influence of current leaking from a transistor for resetting to a photoelectric conversion element, and the driving method of the semiconductor device. SOLUTION: In this semiconductor device and its driving method, the semiconductor device has the transistor for resetting, the photoelectric conversion element, and reset- and diode-side power lines, and the potential of the reset-side power line is brought closer to that of the diode-side power line when the transistor for resetting does not conduct electricity.



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